

IN THE CLAIMS:

Please cancel claims 16-30 without prejudice or disclaimer.

Please add the following new claims:

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C1
- 42. An intermediate semiconductor capacitor structure, comprising:
a storage poly structure;
a hemispherical-grain polysilicon layer on said storage poly structure; and
a mask positioned over the hemispherical-grain polysilicon layer, elevated portions of the hemispherical-grain polysilicon layer being exposed through said mask.
43. An intermediate semiconductor capacitor structure, comprising:
a storage poly structure including recesses formed therein;
a hemispherical-grain polysilicon layer on at least portions of said storage poly structure; and
a mask positioned over the hemispherical-grain polysilicon layer, said recesses in said storage poly structure being exposed through said mask.
44. A semiconductor capacitor structure, comprising:
a storage poly structure with recesses formed therein;
a hemispherical-grain polysilicon layer on at least portions of the storage poly structure; and
dielectric material lining at least said recesses.
45. A semiconductor memory cell, comprising:
a storage poly structure with recesses formed therein;
a hemispherical-grain polysilicon layer on at least portions of the storage poly structure; and
dielectric material at least lining said recesses.--

REMARKS

It is respectfully submitted that new claims 42-45 do not introduce new matter, as similar subject matter was previously recited in claims 16-30, which are withdrawn from consideration and have been canceled herein without prejudice or disclaimer.